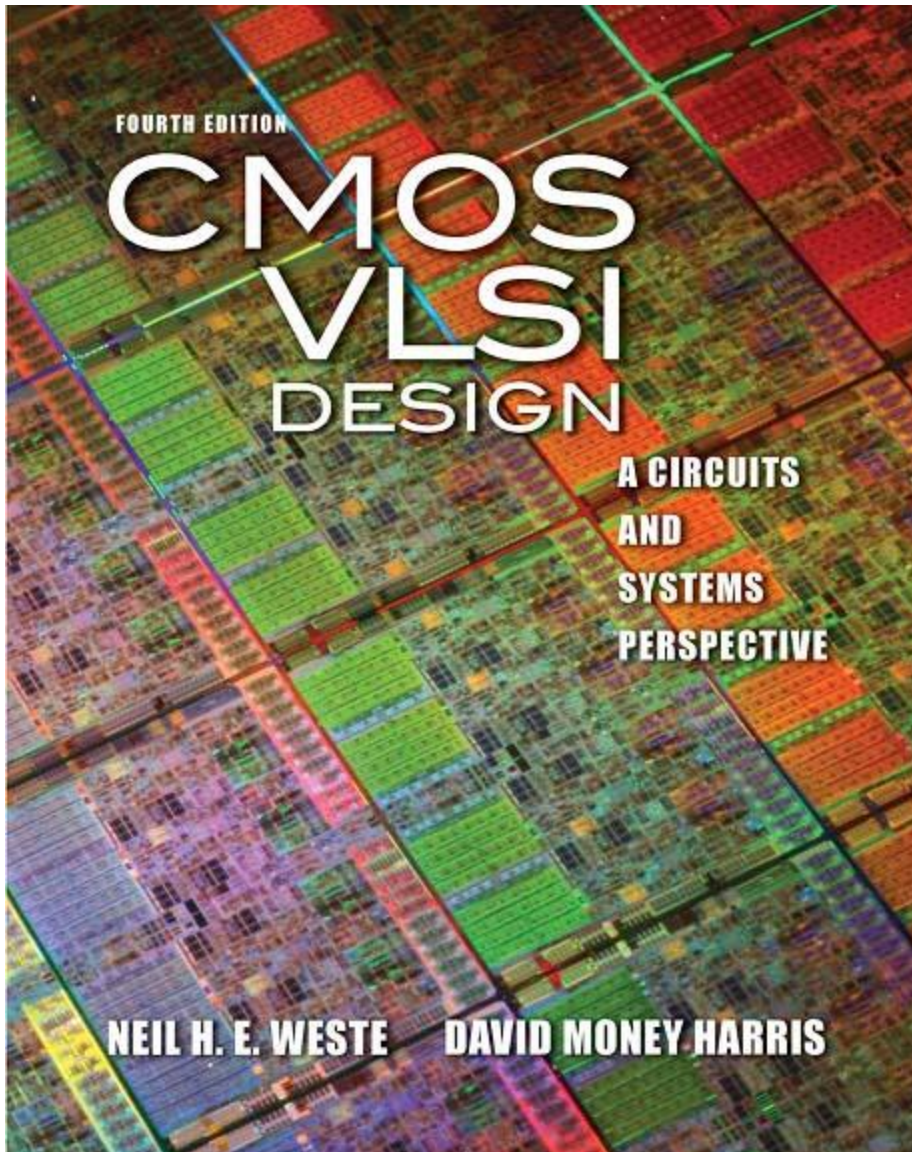


Introduction



Dr. Bassam Jamil

**Adopted from slides of the
textbook**

Outline

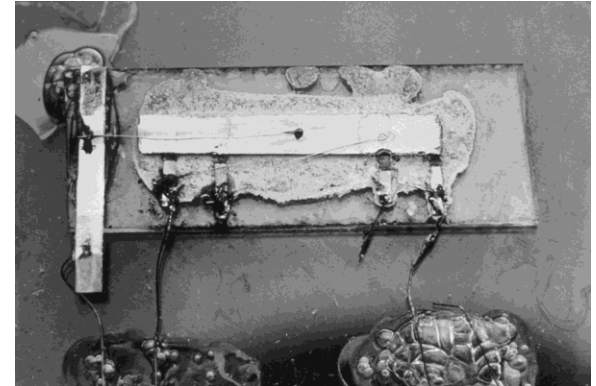
- Brief History
- MOS Transistor

Introduction

- ❑ Integrated circuits: many transistors on one chip.
- ❑ *Very Large Scale Integration (VLSI)*: bucketloads!
- ❑ *Complementary Metal Oxide Semiconductor*
 - Fast, cheap, low power transistors
- ❑ Today: How to build your own simple CMOS chip
 - CMOS transistors
 - Building logic gates from transistors
 - Transistor layout and fabrication
- ❑ Rest of the course: How to build a good CMOS chip

A Brief History

- ❑ 1958: First integrated circuit
 - Flip-flop using two transistors
 - Built by Jack Kilby at Texas Instruments
- ❑ 2010
 - Intel Core i7 μ processor
 - 2.3 billion transistors
 - 64 Gb Flash memory
 - > 16 billion transistors



Courtesy Texas Instruments



[Trinh09]
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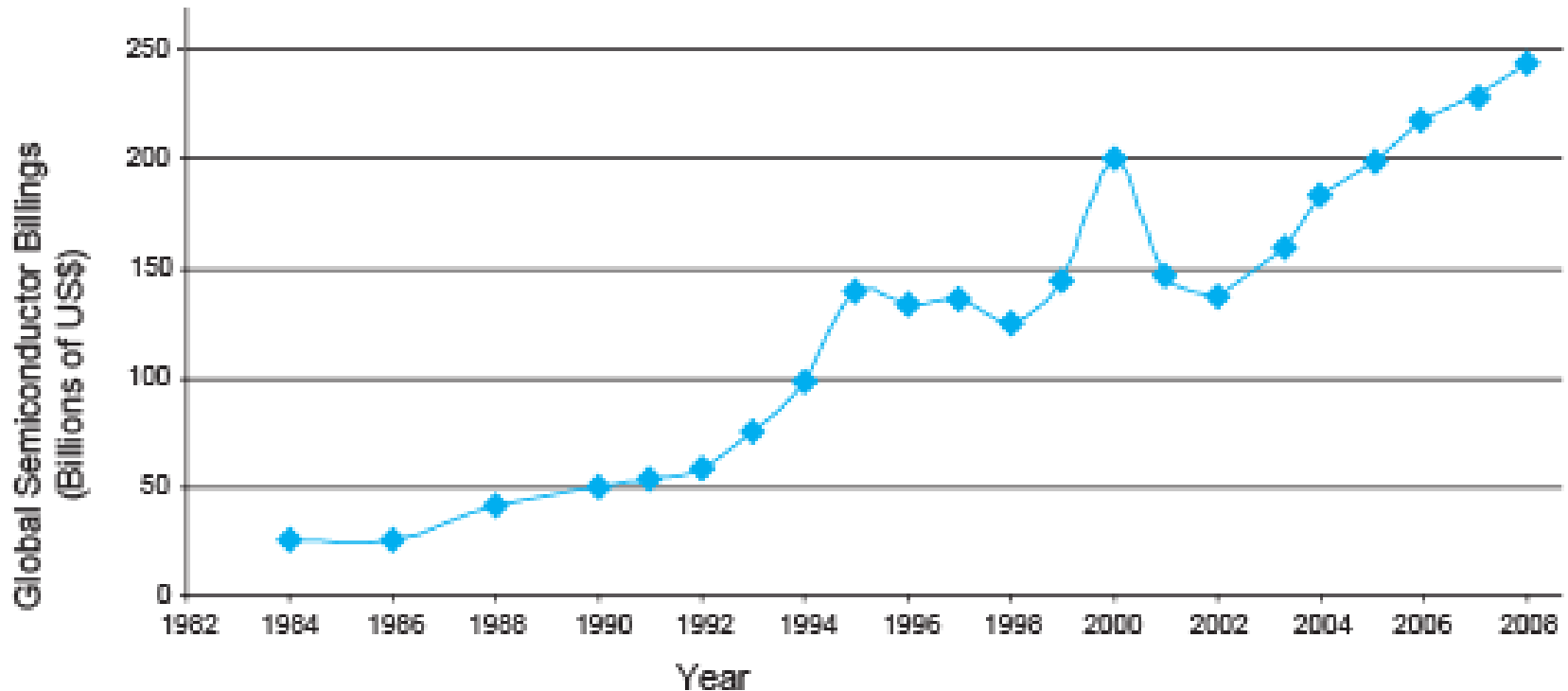
Growth Rate

- ❑ 53% compound annual growth rate over 50 years
 - No other technology has grown so fast so long
- ❑ Driven by miniaturization of transistors
 - Smaller is cheaper, faster, lower in power!
 - Revolutionary effects on society

[Moore65]
Electronics Magazine

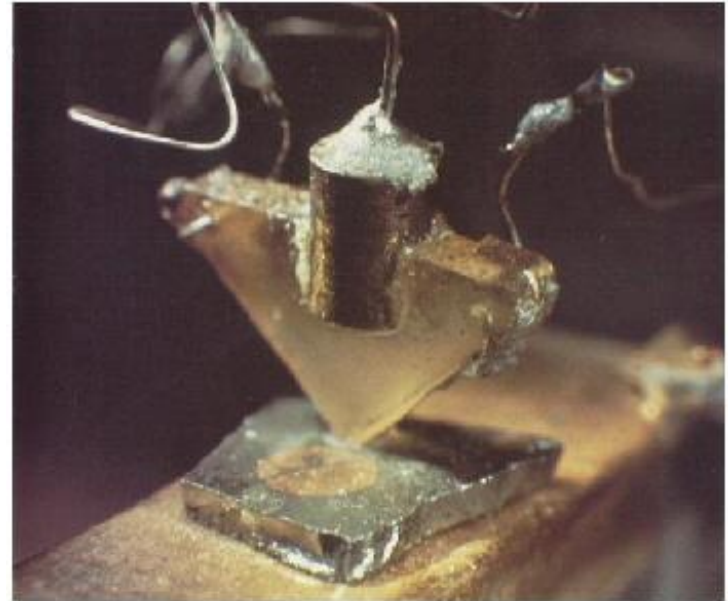
Annual Sales

- ❑ $>10^{19}$ transistors manufactured in 2008
 - 1 billion for every human on the planet



Invention of the Transistor

- ❑ Vacuum tubes ruled in first half of 20th century
Large, expensive, power-hungry, unreliable
- ❑ 1947: first point contact transistor
 - John Bardeen and Walter Brattain at Bell Labs
 - See *Crystal Fire*
by Riordan, Hodgeson



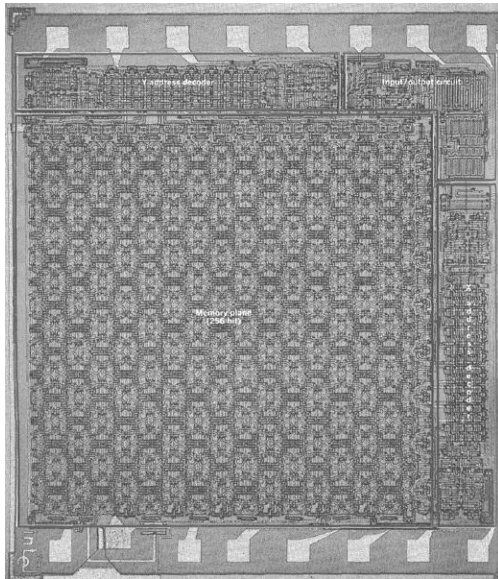
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Transistor Types

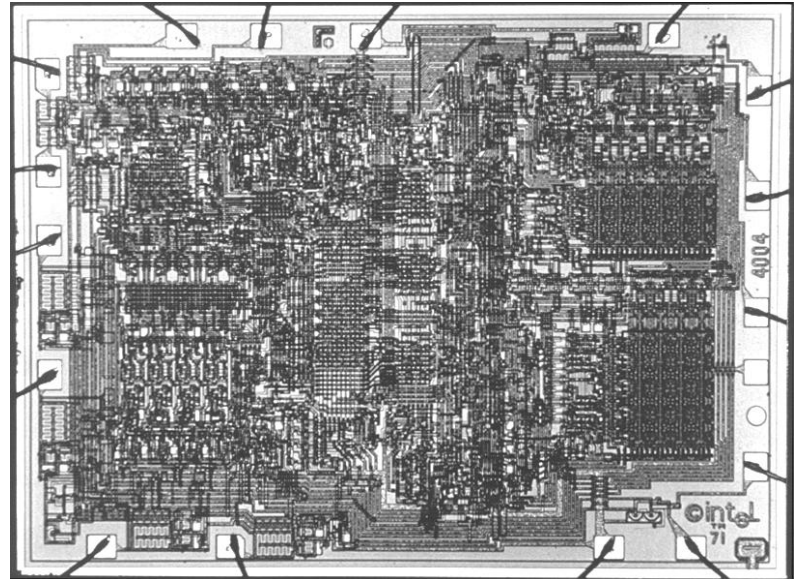
- ❑ Bipolar transistors
 - npn or pnp silicon structure
 - Small current into very thin base layer controls large currents between emitter and collector
 - Base currents limit integration density
- ❑ Metal Oxide Semiconductor Field Effect Transistors
 - nMOS and pMOS MOSFETS
 - Voltage applied to insulated gate controls current between source and drain
 - Low power allows very high integration

MOS Integrated Circuits

- ❑ 1970's processes usually had only nMOS transistors
 - Inexpensive, but consume power while idle



[Vadasz69]
© 1969 IEEE.



Intel Museum.
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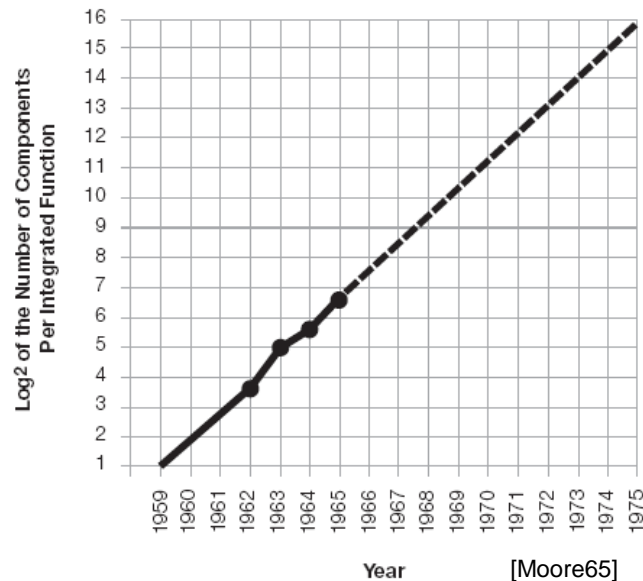
Intel 1101 256-bit SRAM

Intel 4004 4-bit μ Proc

- ❑ 1980s-present: CMOS processes for low idle power

Moore's Law: Then

- ❑ Gordon Moore found transistor count doubling every 18 months



[Moore65]
Electronics Magazine

Integration Levels

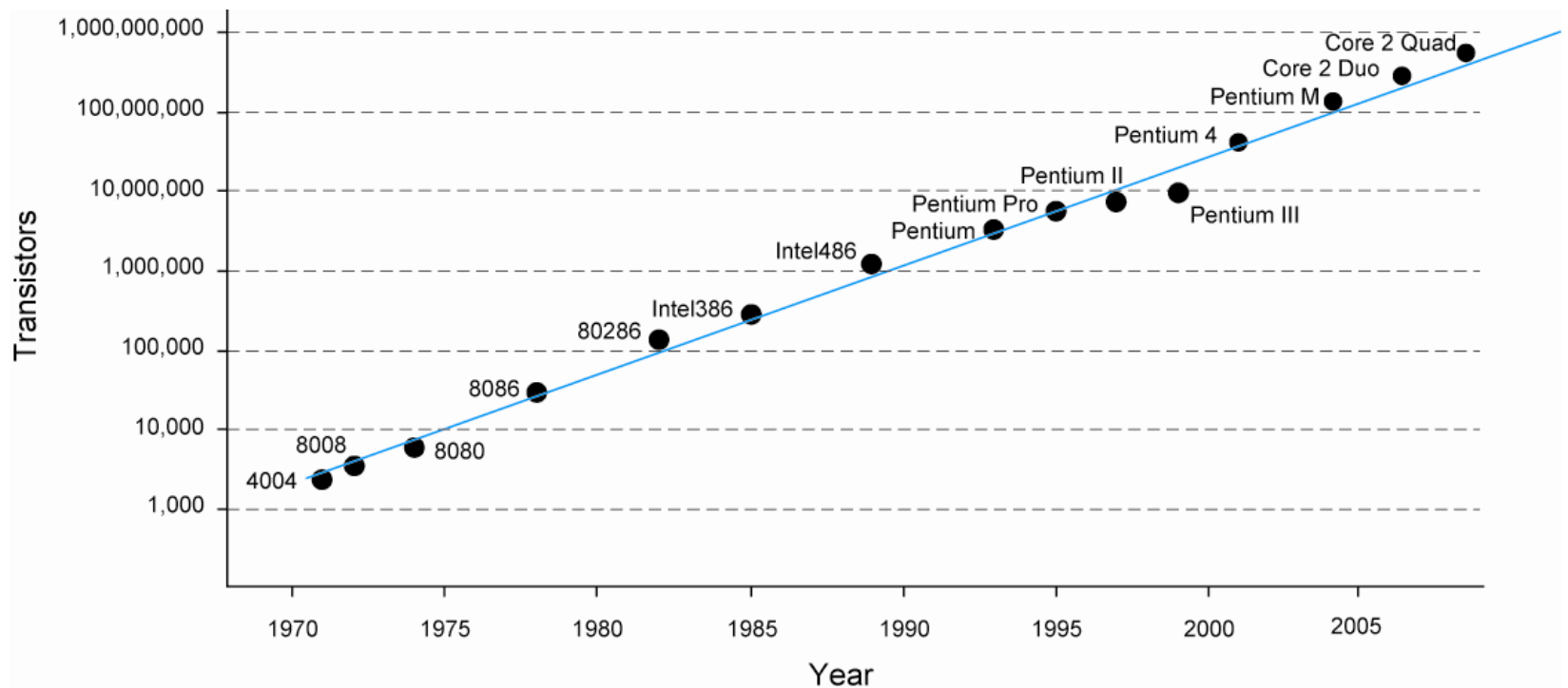
SSI: 10 gates

MSI: 1000 gates

LSI: 10,000 gates

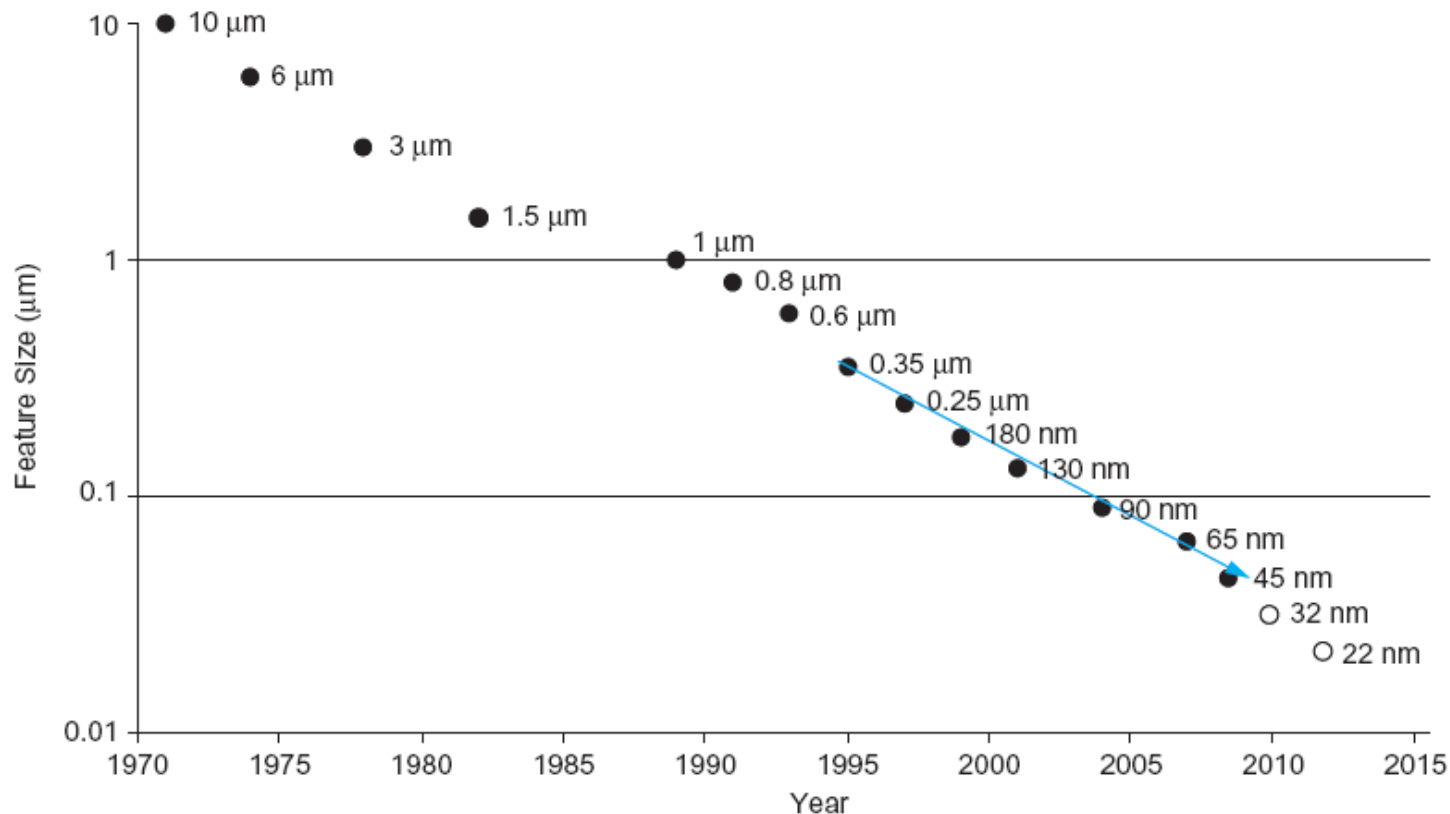
VLSI: > 10k gates

And Now...



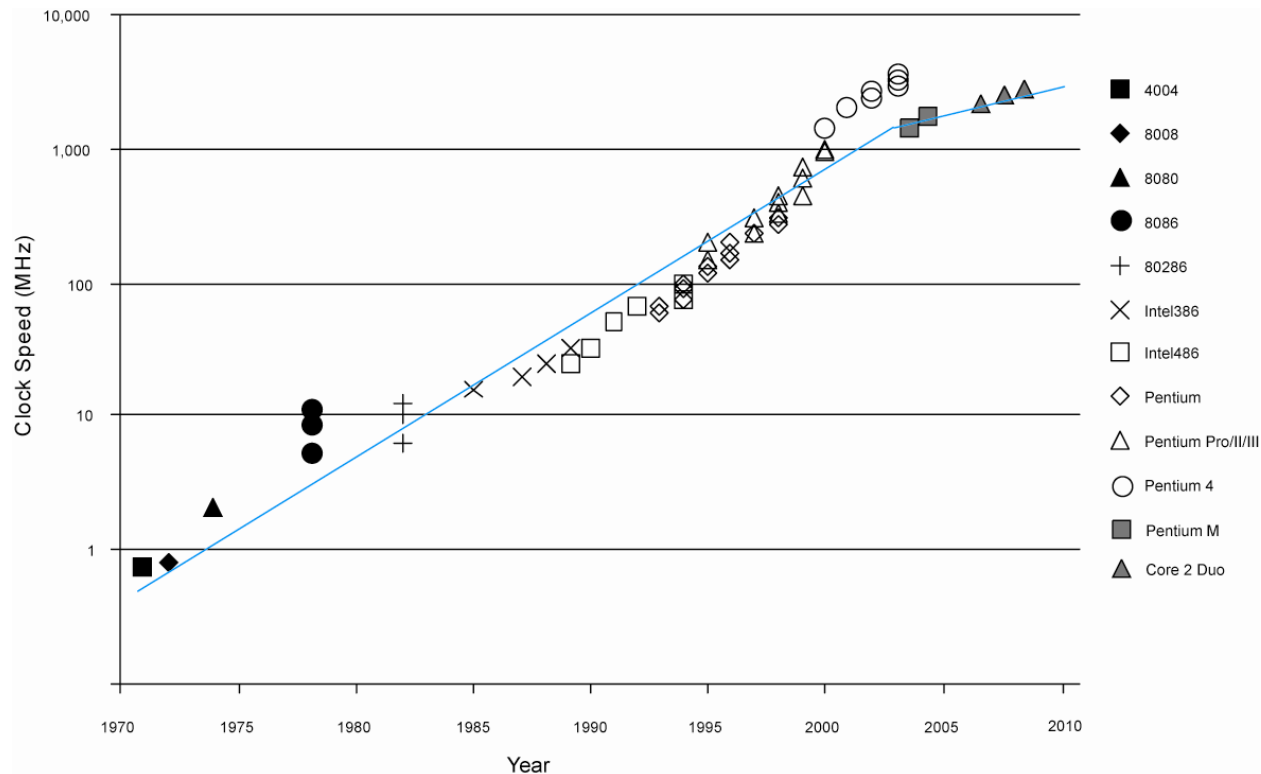
Feature Size

- ❑ Minimum feature size shrinking 30% every 2-3 years



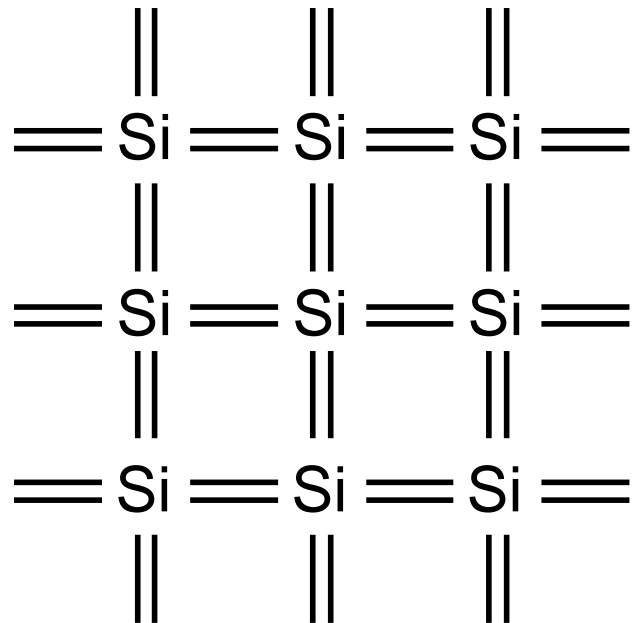
Corollaries

- Many other factors grow exponentially
 - Ex: clock frequency, processor performance



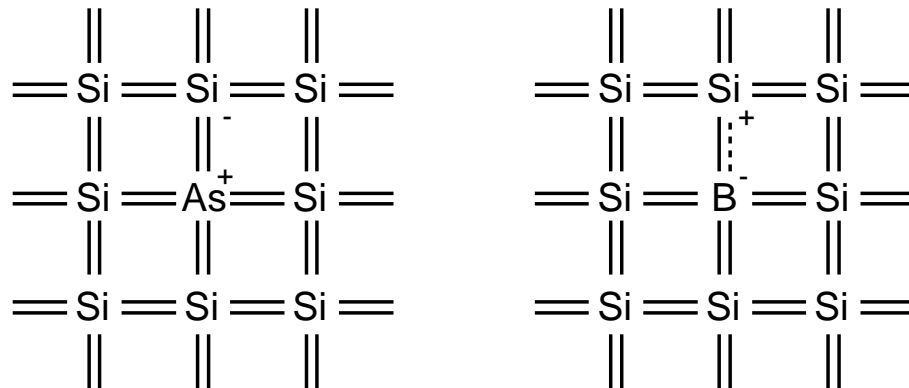
MOS Transistor: Silicon Lattice

- ❑ Transistors are built on a silicon substrate
- ❑ Silicon is a Group IV material
- ❑ Forms crystal lattice with bonds to four neighbors



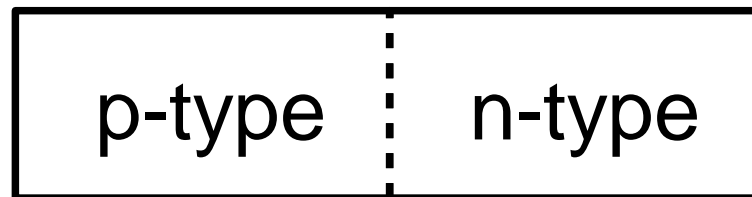
Dopants

- ❑ Silicon is a semiconductor
- ❑ Pure silicon has no free carriers and conducts poorly
- ❑ Adding dopants increases the conductivity
- ❑ Group V: extra electron (n-type)
- ❑ Group III: missing electron, called hole (p-type)



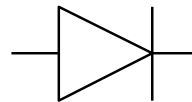
p-n Junctions

- ❑ A junction between p-type and n-type semiconductor forms a diode.
- ❑ Current flows only in one direction



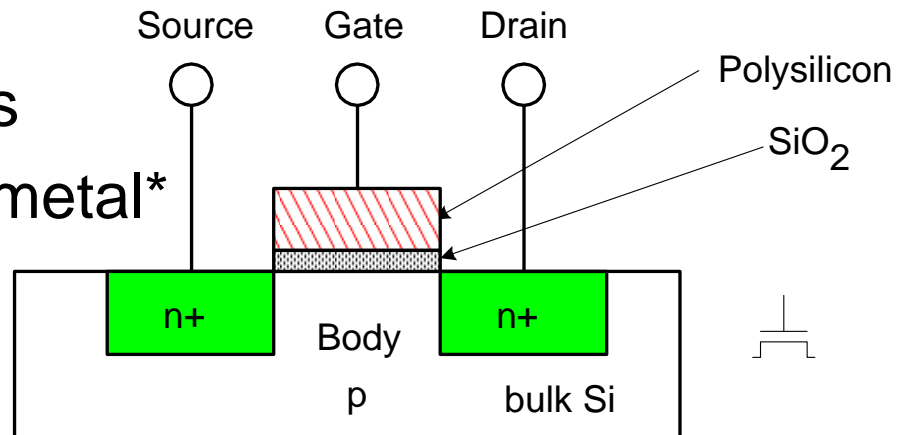
anode

cathode



nMOS Transistor

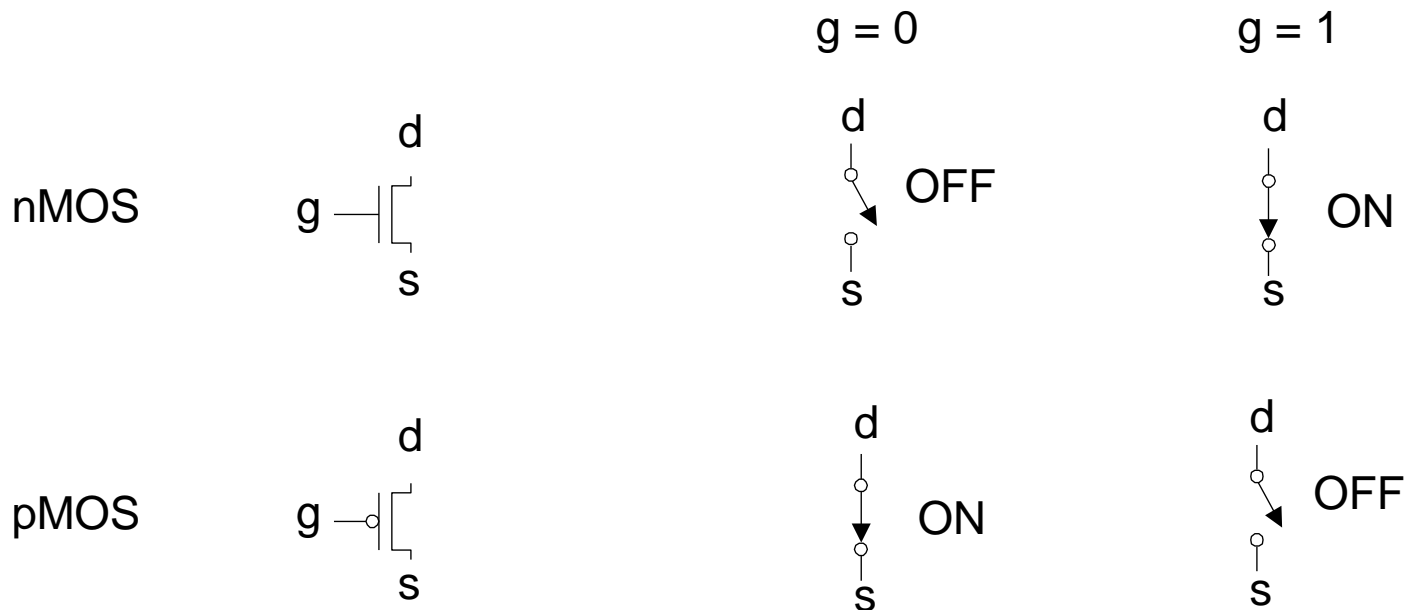
- ❑ Four terminals: gate, source, drain, body
- ❑ Gate – oxide – body stack looks like a capacitor
 - Gate and body are conductors
 - SiO_2 (oxide) is a very good insulator
 - Called metal – oxide – semiconductor (MOS) capacitor
 - Even though gate is no longer made of metal*



* Metal gates are returning today!

Transistors as Switches

- ❑ We can view MOS transistors as electrically controlled switches
- ❑ Voltage at gate controls path from source to drain



CMOS Inverter

A	Y
0	1
1	0

